IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re	U.S. Patent Application of)
SATO	et al.))
Appli	cation Number: To be Assigned)
Filed:	Concurrently Herewith)
For:	MANUFACTURING METHOD OF SEMICONDUCTOR LASER DIODE)))
Атто	RNEY DOCKET NO. NITT.0191)

Honorable Assistant Commissioner for Patents Washington, D.C. 20231

INFORMATION DISCLOSURE STATEMENT

Sir:

Pursuant to 37 C.F.R. §§ 1.56 and 1.97, this Information Disclosure Statement is submitted in the above-identified patent application. A listing of documents to be published on the face of any patent granted from this application is submitted herewith on Form PTO-1449. Any other documents or information submitted for consideration by the Examiner are listed in this paper. A copy of each U.S. and foreign patent, or each publication or portion thereof listed or herein identified, submitted herewith.

This Information Disclosure Statement is submitted with the initial filing of the application. Accordingly, no fee is due or payable at this time.

The Examiner is requested to acknowledge consideration of the information provided in this paper in accordance with prescribed procedures.

Please charge any additional fees or credit any overpayments in connection with this paper to Deposit Account No. 08-1480.

Respectfully submitted,

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February 13, 2004

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